

Notice of References CitedApplication/Control No.
09/522,707Applicant(s)/Patent Under Reexam
Hiramatsu et al.Examiner
B. William BaumeisterArt Unit
2815

Page 1 of 2

U.S. PATENT DOCUMENTS

	Document Number Country Code-Number-Kind Code	Date MM-YYYY ¹	Name	Classification ²	
A	6,153,010	11/2000	Kiyoku et al.	117	95
B	6,325,850	12/2001	Beaumont et al.	117	95
C	5,880,485	3/1999	Marx et al.	257	94
D	6,177,688	1/2001	Linthicum et al.	257	77
E	6,051,849	4/2000	Davis et al.	257	103
F	5,874,747	2/1999	Redwing et al.	257	77
G					
H					
I					
J					
K					
L					
M					

FOREIGN PATENT DOCUMENTS

	Document Number Country Code-Number-Kind Code	Date MM-YYYY ¹	Country	Name	Classification ²	
N						
O						
P						
Q						
R						
S						
T						

NON-PATENT DOCUMENTS

	Include, as applicable: Author, Title, Date, Publisher, Edition or Volume, Pertinent Pages
U	Nakamura et al., "Long lifetime violet InGaN/GaNAlGaIn-based semiconductor lasers," 5/28/1998, pp. 52-58.
V	Yu, et al., "Study of the epitaxial-lateral-overgrowth (ELOO) process for GaN on sapphire," Journal of Crystal Growth 195 (1998) 333-339.
W	Sakai et al., "Defect structure in selectively grown GaN films with low threading dislocation density," Appl. Phys. Lett. 71 (1997) 20 October 1997, pp. 2259-2261.
X	Wong et al., "Damage-free separation of GaN thin films from sapphire substrates," Appl. Phys. Lett. 72 (5), 2 February 1998, pp. 599-601.

¹ A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(a).¹ Dates in MM-YYYY format are publication dates.² Classifications may be U.S. or foreign.

Notice of References CitedApplication/Control No.
09/522,707Inventor(s)/Patent Under Reexam
Hiramatsu et al.Examiner
B. William BaumeisterArt Unit
2815

Page 2 of 2

U.S. PATENT DOCUMENTS

		Document Number Country Code-Number-Kind Code	Date MM-YYYY ¹	Name	Classification ²
	A				
	B				
	C				
	D				
	E				
	F				
	G				
	H				
	I				
	J				
	K				
	L				
	M				

FOREIGN PATENT DOCUMENTS

		Document Number Country Code-Number-Kind Code	Date MM-YYYY ¹	Country	Name	Classification ²
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

		Include, as applicable: Author, Title, Date, Publisher, Edition or Volume, Pertinent Pages
	U	Jones et al., "Characteristics of GaN Stripes Grown by Selective-Area Metalorganic Chemical Vapor Deposition," Journal of Electronic Materials, Vol. 26, No. 3, 1997, pp. 306-310.
	V	
	W	
	X	

¹ A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(a).¹ Dates in MM-YYYY format are publication dates.² Classifications may be U.S. or foreign.